

60V N-Channel Power MOSFET



TO-220

ITO-220

Pin Definition:

1. Gate 2. Drain

3. Source

Key Parameter Performance

Parameter		Value	Unit	
V_{DS}		60	V	
R _{DS(on)} (max)	V _{GS} = 10V	23		
	V _{GS} = 4.5V	28	mΩ	
Q _q		28	nC	



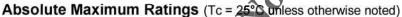


Features

- 100% avalanche tested
- Fast Switching

Ordering Information

- L	,	w 2		
1		1	Q_g	28
TO-252		- -		•
(DPAK)				
2				
2 3			(3)	
1			3	
		, O	Disabil	D:
<u>Features</u>			Block	<u>Diagram</u>
 100% avalanche teste 	ed			Drain
 Fast Switching 		100		9
Ordering Informatio	n		100	
Ordering informatio	<u>''</u>	0> 0		
Part No.	Package	Packing		البر
TSM230N06CZ C0G	TO-220	50pc s / Tub e	Tended Gate o-	⊿i≒ ↑
TSM230N06CI C0G	JTO 220	50pcs / Tube		
TSM230N06CP ROG	TO-252	2.5kpcs / 13" Reel		
Note: "G" denotes for Halogen	- and Antimony-	free as those which contain		Y
<900ppm bromine, <900 <1000ppm antimony co		1500ppm total Br + Cl) and		Source
			N-Channe	el MOSFET



Parameter		Symbol		1124		
			TO-220	ITO-220	DPAK	Unit
Drain-Source Voltage		V_{DS}		V		
Gate-Source Voltage		V_{GS}		V		
Continuous Drain Current (Note 1)	Tc = 25°C	I _D	50*			Α
	Tc = 100°C		32*			Α
Pulsed Drain Current (Note 2)		I _{DM}	200			Α
Single Pulse Avalanche Energy (Note 3)		E _{AS}	42			mJ
Power Dissipation @ T _C = 25°C		P_{D}	104	42	53	W
Operating Junction Temperature		TJ	150			°C
Storage Temperature Range		T_{STG}	-55 to +150			°C



60V N-Channel Power MOSFET



Thermal Performance

	0 1 1		11-14			
Parameter	Symbol	TO-220	ITO-220	DPAK	Unit	
Thermal Resistance - Junction to Case	R _{eJC}	1.2	3	2	0000	
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	62	62	°C/W	

Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	60			V
Drain Course On State Decistance	$V_{GS} = 10V, I_D = 20A$			20	23	~~ 0
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 12A$	R _{DS(ON)}		23	28	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1.2	1.8	2.5	V
Zero Gate Voltage Drain Current	V _{DS} = 60V, V _{GS} = 0V	~0			1	
Zero Gate Voltage Drain Current	V _{DS} = 48V, T ₁ = 125°C	I _{DSS}			10	μA
Gate Body Leakage	$V_{GS} = \pm 20V$, $V_{DS} = 0V$) I _{GSS}	A		±100	nA
Forward Transconductance (Note 4)	$V_{DS} = 10V, I_{D} = 10A$	g _{fs}	2-	9		S
Dynamic	· O > O		Y			
Total Gate Charge (Note 4,5)	$V_{DS} = 30V, I_{Q} = 15A,$	Qg		28		
Gate-Source Charge (Note 4,5)		Qgs		3.5		nC
Gate-Drain Charge (Note 4,5)	V _{GS} = 10V	Q_{gd}		6.5		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V$	C _{iss}		1680		
Output Capacitance	t = 1.0 MHz	C _{oss}		115		pF
Reverse Transfer Capacitance	57 1.0IVII 12	C_{rss}		85		
Switching	X					
Turn-On Delay Time (Note 4,5))	40	t _{d(on)}		7.2		
Turn-On Rise Time (Note 4,5))	$V_{DD} = 30V, I_D = 1A,$	t _r		38		ne
Turn-Off Delay Time (Note 4,5)	$V_{GS} = 10V, R_G = 6\Omega$	t _{d(off)}		34		ns
Turn-Off Fall Time (Note 4,5)		t _f		8.2		
Source-Drain Diode Ratings and Ch	aracteristic					
Maximum Continuous Drain-Source		,			50	Α
Diode Forward Current	Integral reverse diode	I _S			30	
Maximum Pulse Drain-Source Diode	in the MOSFET	I _{SM}			200	A
Forward Current		ISM			200	
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V_{SD}			1	V
Reverse Recovery Time (Note 4)	$V_{GS} = 0V, I_{S} = 1A$	t _{rr}		19.6		ns
Reverse Recovery Charge (Note4)	$dI_F/dt = 100A/\mu s$	Q_{rr}		14.2		nC

Note:

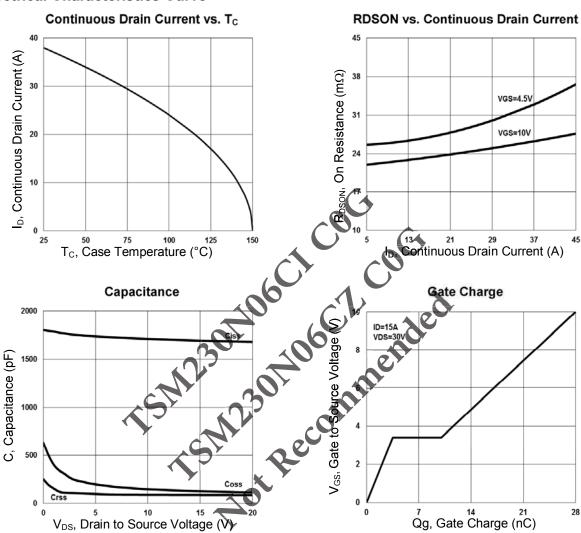
- 1. Limited by maximum junction temperature
- 2. Pulse width limited by safe operating area
- 3. L = 0.1mH, I_{AS} = 29A, V_{DD} = 25V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C
- 4. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 5. Switching time is essentially independent of operating temperature.



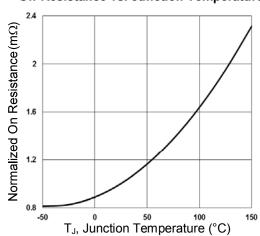
60V N-Channel Power MOSFET



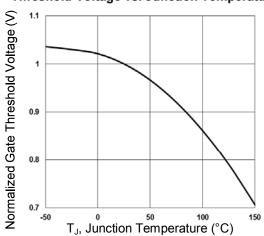
Electrical Characteristics Curve



On-Resistance vs. Junction Temperature



Threshold Voltage vs. Junction Temperature



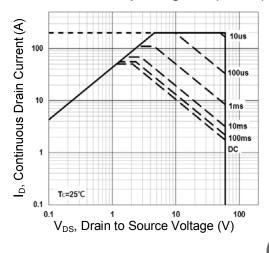


60V N-Channel Power MOSFET

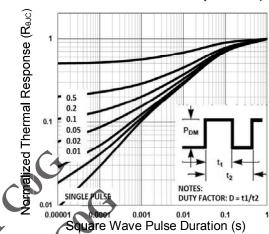


Electrical Characteristics Curve

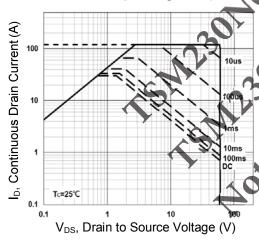
Maximum Safe Operating Area (TO-220)



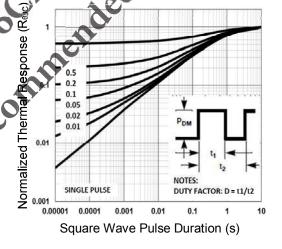
Normalized Thermal Transient Impedance (TO-220)



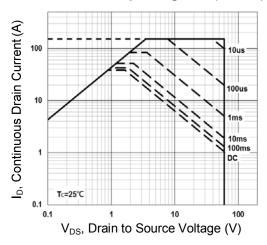
Maximum Safe Operating Area (ITO-220)



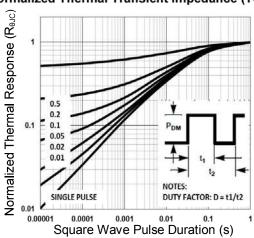
Normalized Thermal Transient Impedance (ITO-220)



Maximum Safe Operating Area (TO-252)



Normalized Thermal Transient Impedance (TO-252)



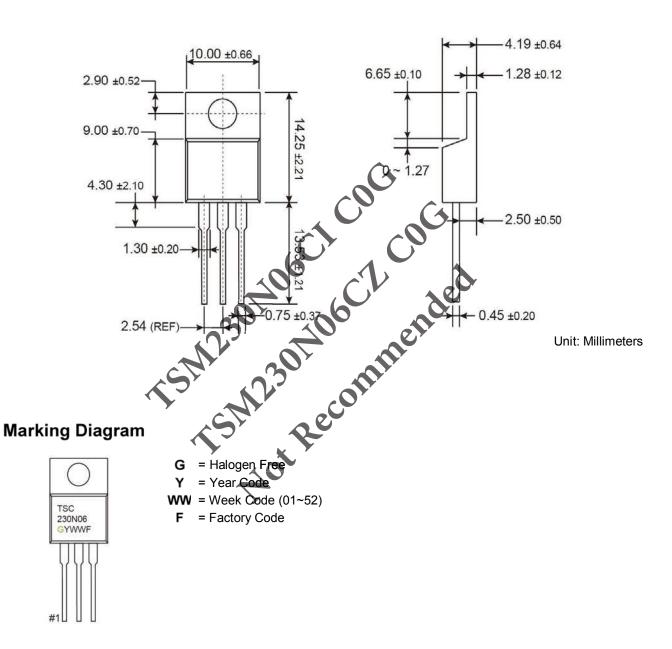






60V N-Channel Power MOSFET

TO-220 Mechanical Drawing



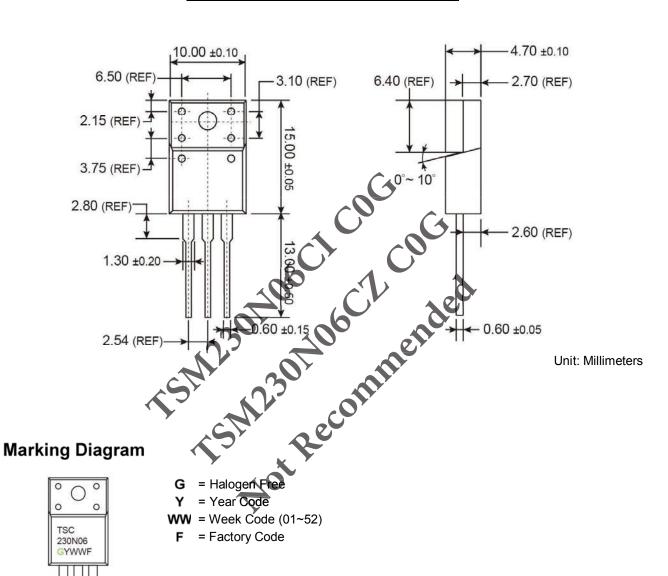






60V N-Channel Power MOSFET

ITO-220 Mechanical Drawing

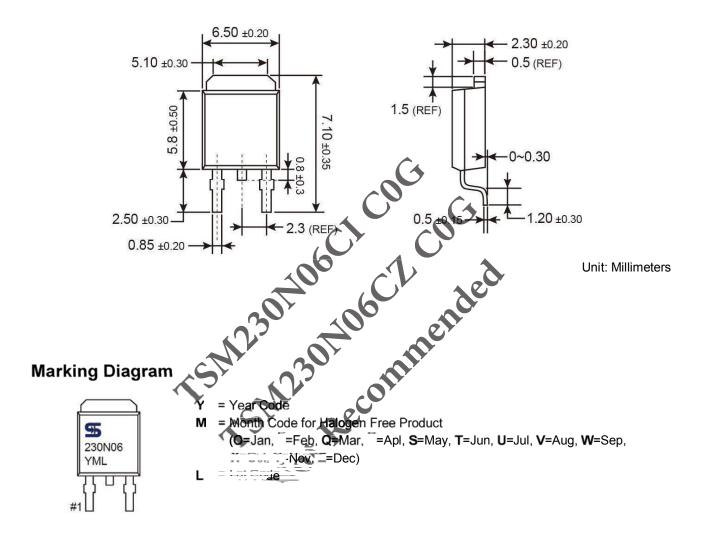




60V N-Channel Power MOSFET



TO-252 Mechanical Drawing





60V N-Channel Power MOSFET



Ash Reconninented Ash Reconninented

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.